

SuperMOS – SOT-23 -30V BV_{DSS} , 46m Ω $R_{DS(on)}$, P-channel MOSFET

1. Description

The SI2347DS-T1-GE3(ES) is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product SI2347DS-T1-GE3(ES) is Pb-free.

2. Features

- 30V, $R_{DS(ON)}$ =46m Ω (Typ.) @ V_{GS} =-10V
 $R_{DS(ON)}$ =62m Ω (Typ.) @ V_{GS} =-4.5V
- Fast Switching
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
SI2347DS-T1-GE3(ES)	SOT-23	R7	Halogen free	Tape & Reel	3,000 PCS	UL 94V-0	7 inches

Table-1 Ordering information

5. Pin Configuration and Functions

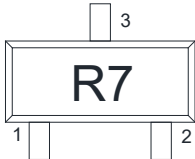
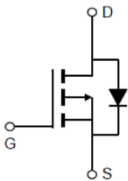
Pin	Function	Outline	Circuit Diagram
1	Gate		
2	Source		
3	Drain		

Table-2 Pin configuration

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	-30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_A=25^{\circ}\text{C}$	I_D	-3.8	A
	$T_A=75^{\circ}\text{C}$		-2.9	
Maximum Power Dissipation	$T_A=25^{\circ}\text{C}$	P_D	1.4	W
Pulsed Drain Current		I_{DM}	-15.2	A
Operating Junction Temperature		T_J	150	$^{\circ}\text{C}$
Storage Temperature Range		T_{stg}	-55 to +150	$^{\circ}\text{C}$

Thermal resistance ratings

Single Operation				
Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance	$R_{\theta JA}$		90	$^{\circ}\text{C/W}$

SI2347DS-T1-GE3(ES)

Rev-1.2

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-1	uA
Gate-to-source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =-250uA	-0.9	-1.5	-2.0	V
Drain-to-source On-resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-3A		46	60	mΩ
		V _{GS} =-4.5V, I _D =-3A		62	80	
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =-15V, f=1MHz		550		pF
Output Capacitance	C _{OSS}			75		
Reverse Transfer Capacitance	C _{RSS}			63		
Total Gate Charge	Q _{G(TOT)}	V _{GS} =-10V, V _{DS} =-15V, I _D =-4A		6.5		nC
Gate-to-Source Charge	Q _{GS}			1.1		
Gate-to-Drain Charge	Q _{GD}			1.3		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{d(ON)}	V _{GS} =-10V, V _{DS} =-15V, R _L =3.5Ω, R _G =3Ω		14		ns
Rise Time	t _r			60		
Turn-Off Delay Time	t _{d(OFF)}			19		
Fall Time	t _f			11		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-1.0A		-0.7	-1.5	V

7. Typical Characteristic

Figure 1. On-Regin Characteristics

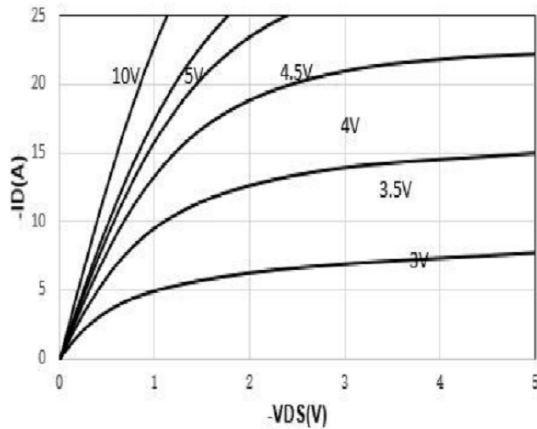


Figure 2. Transfer Characteristics

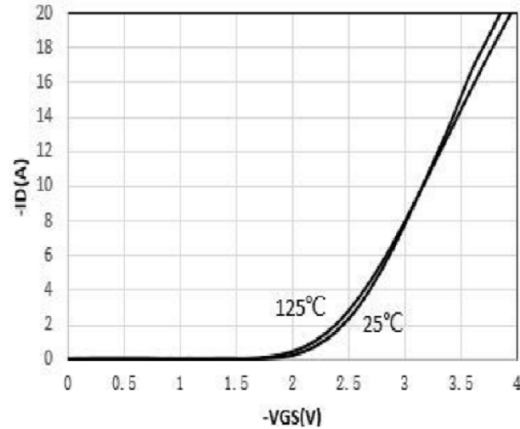


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

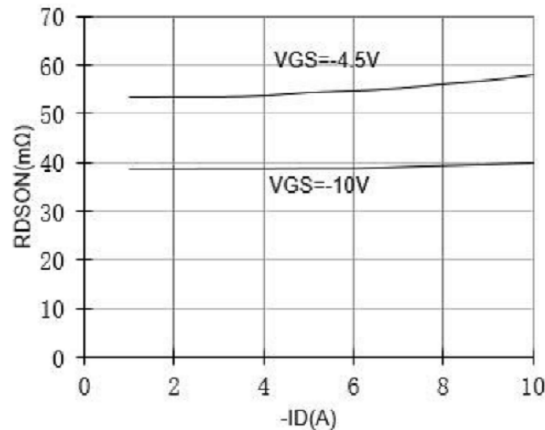


Figure 4. On-Resistance vs. Junction Temperature

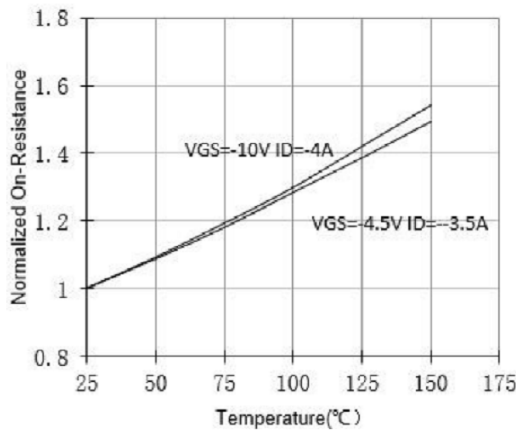


Figure 5. On-Resistance vs. Gate-Source Voltage

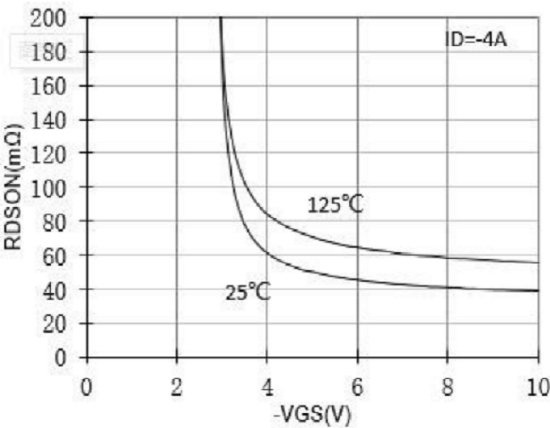


Figure 6. Body-Diode Characteristics

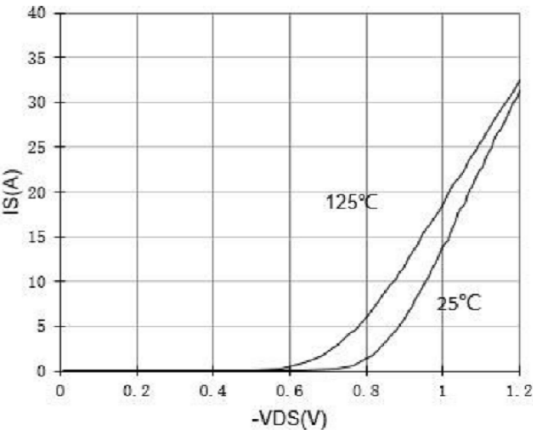


Figure 7. Gate-Charge Characteristics

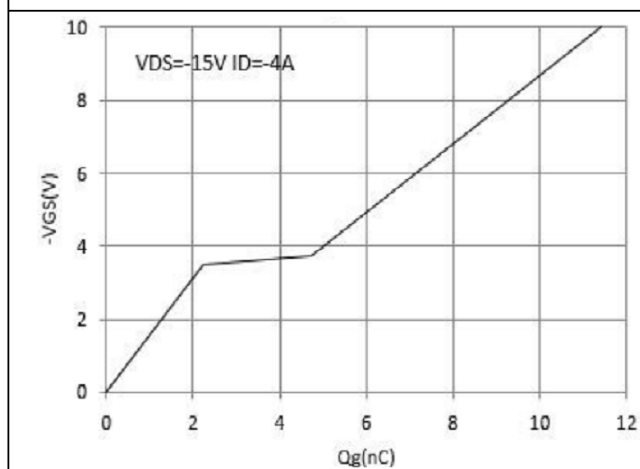


Figure 8. Capacitance Characteristics

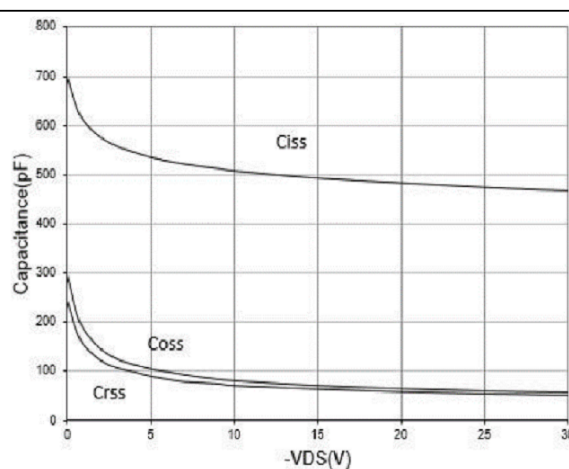


Figure 9. Maximum Forward Biased Safe Operating Area

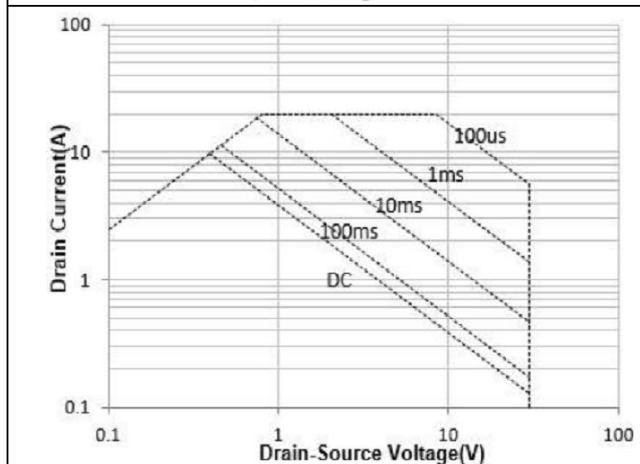


Figure 10. Single Pulse Power Rating Junction-to-Ambient

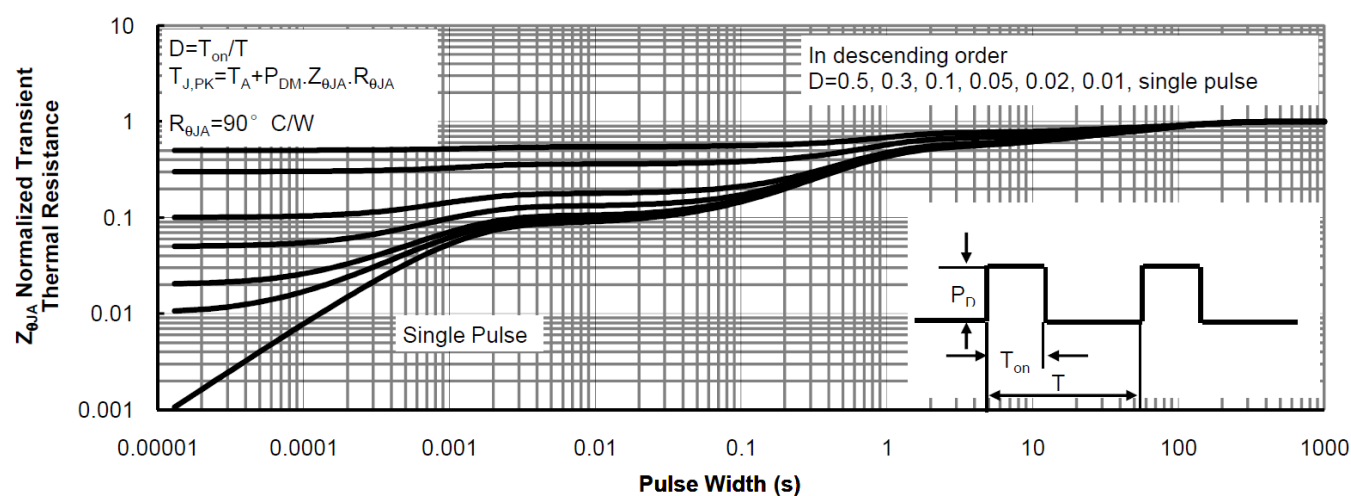
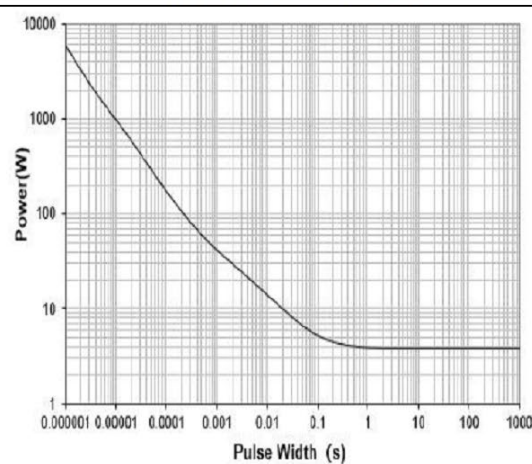
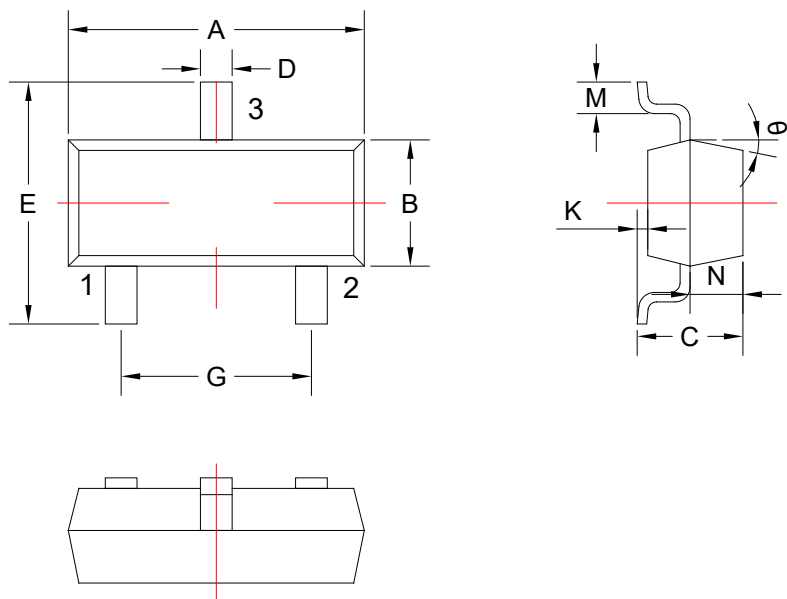


Figure 11: Normalized Maximum Transient Thermal Impedance

8. Dimension (SOT-23)



COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER					
SYMBOL	MIN	MAX	SYMBOL	MIN	MAX
A	2.85	3.04	G	1.80	2.00
B	1.20	1.40	K	0	0.10
C	0.90	1.10	M	0.20	-
D	0.40	0.50	N	0.50	0.70
E	2.25	2.55	θ	5°	9°

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